

Notice of References Cited	Application/Control No.	Applicant(s)/Patent Under Reexamination	
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	Examiner	Art Unit	Page 1 of 1
	Mai-Huong Tran	2818	

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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NON-PATENT DOCUMENTS

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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.